

NPN SILICON RF TRANSISTOR

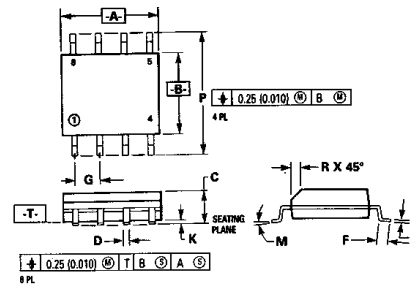
DESCRIPTION:

The **ASI MRF4427** is Designed for General Purpose Amplifier and Oscillator in VHF and UHF applications.

MAXIMUM RATINGS

I_C	400 mA
V_{CEO}	20 V
V_{CBO}	40 V
V_{EBO}	4.0 V
P_{DISS}	1.5 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+150^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	125 $^\circ\text{C/W}$

PACKAGE STYLE



STYLE 1:
PIN 1: EMITTER
2: COLLECTOR
3: COLLECTOR
4: EMITTER
5: EMITTER
6: BASE
7: BASE
8: EMITTER



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.196
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.18	0.25	0.007	0.009
K	0.10	0.25	0.004	0.009
M	0"	7"	0"	7"
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 5.0\text{ mA}$		20			V
BV_{CER}	$I_C = 5.0\text{ mA}$	$R_{BE} = 10\ \Omega$	40			V
BV_{EBO}	$I_E = 100\ \mu\text{A}$		2.0			V
I_{CEO}	$V_{CB} = 12\text{ V}$				20	μA
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 100\text{ mA}$	10	50	200	---
	$V_{CE} = 5.0\text{ V}$	$I_C = 360\text{ mA}$	5.0			
$V_{CE(sat)}$	$I_C = 50\text{ mA}$	$I_B = 20\text{ mA}$		60		mV
C_{OB}	$V_{CB} = 12\text{ V}$	$f = 1.0\text{ MHz}$			3.0	pF
f_t	$V_{CE} = 12\text{ V}$	$I_C = 50\text{ mA}$		1600		MHz
G_{pe}	$V_{CC} = 12\text{ V}$	$P_{IN} = 15\text{ mW}$		18		dB
η	$P_{OUT} = 1.0\text{ W}$	$I_C = 50\text{ mA}$		60		%
$ S_{21} ^2$			14	16.4		dB

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